

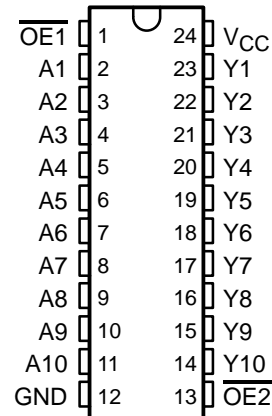
# SN64BCT2827C

## 10-BIT BUS/MOS MEMORY DRIVER WITH 3-STATE OUTPUTS

SCBS415 – APRIL 1987 – REVISED NOVEMBER 1993

- State-of-the-Art BiCMOS Design Significantly Reduces  $I_{CCZ}$
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model ( $C = 200$  pF,  $R = 0$ )
- Output Ports Have Equivalent  $33\text{-}\Omega$  Series Resistors, So No External Resistors Are Required
- High-Impedance State During Power Up and Power Down
- 3-State Outputs Drive Bus Lines or Buffer-Memory Address Registers
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic Small-Outline (DW) Packages and Standard Plastic 300-mil DIPs (NT)

DW OR NT PACKAGE  
(TOP VIEW)



### description

This 10-bit buffer and bus/MOS driver provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ( $\overline{OE1}$  or  $\overline{OE2}$ ) input is high, all ten outputs are in the high-impedance state. The outputs are also in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down.

The outputs, which are designed to source or sink up to 12 mA, include  $33\text{-}\Omega$  series resistors to reduce overshoot and undershoot.

The SN64BCT2827C is characterized for operation from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  and  $0^{\circ}\text{C}$  to  $70^{\circ}\text{C}$ .

FUNCTION TABLE

INPUTS			OUTPUT Y
$\overline{OE1}$	$\overline{OE2}$	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

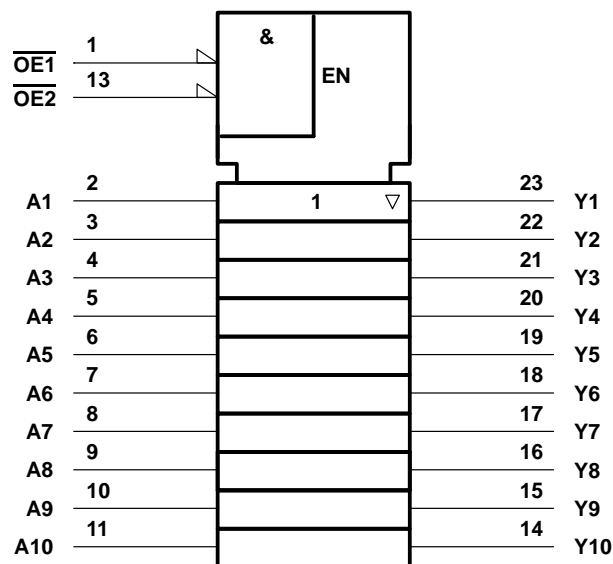
# SN64BCT2827C

## 10-BIT BUS/MOS MEMORY DRIVER

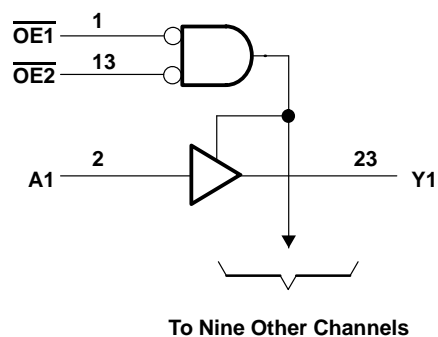
### WITH 3-STATE OUTPUTS

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#### logic symbol†

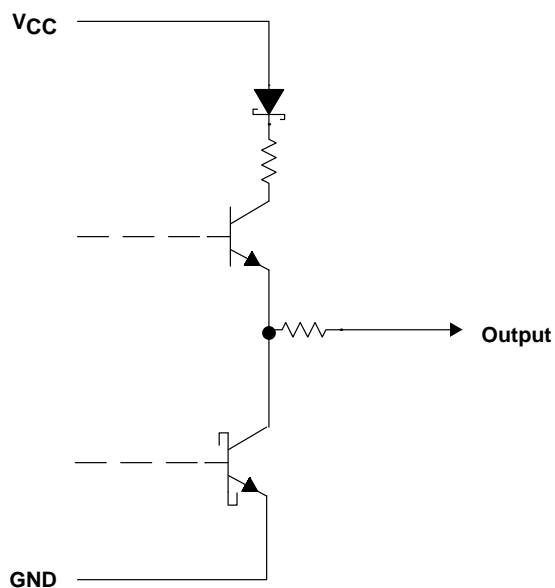


#### logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

#### schematic of each output



**SN64BCT2827C**  
**10-BIT BUS/MOS MEMORY DRIVER**  
**WITH 3-STATE OUTPUTS**

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**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

Supply voltage range, $V_{CC}$	–0.5 V to 7 V
Input voltage range, $V_I$ (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the disabled or power-off state, $V_O$	–0.5 V to 5.5 V
Voltage range applied to any output in the high state, $V_O$	–0.5 V to $V_{CC}$
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	–30 mA
Current into any output in the low state, $I_O$	24 mA
Operating free-air temperature range	–40°C to 85°C
Storage temperature range	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input negative-voltage rating may be exceeded if the input clamp-current rating is observed.

**recommended operating conditions (see Note 2)**

	MIN	NOM	MAX	UNIT
$V_{CC}$ Supply voltage	4.5	5	5.5	V
$V_{IH}$ High-level input voltage	2			V
$V_{IL}$ Low-level input voltage			0.8	V
$I_{IK}$ Input clamp current			–18	mA
$I_{OH}$ High-level output current			–1	mA
$I_{OL}$ Low-level output current			12	mA
$\Delta t/\Delta V_{CC}$ Power-up ramp rate	2			μs/V
$T_A$ Operating free-air temperature	–40		85	°C

NOTE 2: Unused or floating inputs must be held high or low.

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS		MIN	TYP‡	MAX	UNIT
$V_{IK}$	$V_{CC} = 4.5$ V,	$I_I = -18$ mA			–1.2	V
$V_{OH}$	$V_{CC} = 4.5$ V to 5.5 V,	$I_{OH} = -1$ mA	$V_{CC} - 2$			V
$V_{OL}$	$V_{CC} = 4.5$ V	$I_{OL} = 1$ mA		0.15	0.5	V
		$I_{OL} = 12$ mA		0.35	0.8	
$I_I$	$V_{CC} = 5.5$ V,	$V_I = 7$ V		0.1		mA
$I_{IH}$	$V_{CC} = 5.5$ V,	$V_I = 2.7$ V		20		μA
$I_{IL}$	$V_{CC} = 5.5$ V,	$V_I = 0.5$ V		–0.2		mA
$I_{OZ}$	$V_{CC} = 0$ to 2.3 V (power up)	$V_O = 2.7$ or 0.5 V, $\overline{OE} = 0.8$ V		±20		μA
	$V_{CC} = 1.8$ to 0 (power down)			±20		
$I_{OZH}$	$V_{CC} = 5.5$ V,	$V_O = 2.7$ V		20		μA
$I_{OZL}$	$V_{CC} = 5.5$ V,	$V_O = 0.5$ V		–20		μA
$I_{OL(sink)}$	$V_{CC} = 4.5$ V,	$V_O = 2$ V	50			mA
$I_O^{\S}$	$V_{CC} = 5.5$ V,	$V_O = 2.25$ V	–30		–112	mA
$I_{CCL}$	$V_{CC} = 5.5$ V,	Outputs open		28	40	mA
$I_{CCZ}$	$V_{CC} = 5.5$ V,	Outputs open		3.8	6	mA
$C_i$	$V_{CC} = 5$ V,	$V_I = V_{CC}$ or GND		5		pF
$C_o$	$V_{CC} = 5$ V,	$V_O = V_{CC}$ or GND		8		pF

‡ All typical values are at  $V_{CC} = 5$  V,  $T_A = 25^\circ\text{C}$ .

§ The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current,  $I_{OS}$ .



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## 10-BIT BUS/MOS MEMORY DRIVER

### WITH 3-STATE OUTPUTS

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switching characteristics over recommended range of supply voltage,  $C_L = 50 \text{ pF}$  (unless otherwise noted) (see Note 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5 \text{ V}$ , $T_A = 25^\circ\text{C}$			$T_A = -40^\circ\text{C}$ to $85^\circ\text{C}$		$T_A = 0^\circ\text{C}$ to $70^\circ\text{C}$		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$t_{PLH}$	A	Y	0.9	3.6	5.2	0.9	6.6	0.9	6	ns
$t_{PHL}$			2	5.1	7.2	2	8.2	2	7.8	
$t_{PZH}$	$\overline{OE}$	Y	2.8	5.6	8	2.8	11.5	2.8	10.7	ns
$t_{PZL}$			5	8.9	11	5	13.7	5	12.9	
$t_{PHZ}$	$\overline{OE}$	Y	3.2	6.7	10.5	3.2	14	3.2	13	ns
$t_{PLZ}$			2.7	5.3	8.5	2.7	11	2.7	10	

NOTE 3: Load circuits and voltage waveforms are shown in Section 1.



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